## Sensitive Gate Silicon Controlled Rectifiers

## **Reverse Blocking Thyristors**

PNPN devices designed for line powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in surface mount package for use in automated manufacturing.

#### Features

- Sensitive Gate Trigger Current
- Blocking Voltage to 600 V
- Glass Passivated Surface for Reliability and Uniformity
- Surface Mount Package
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (Sine Wave, $R_{GK} = 1 \ k\Omega$ $T_{,1} = 25 \text{ to } 110^{\circ}\text{C}$ )	V <sub>DRM,</sub> V <sub>RRM</sub>		V
MCR08B MCR08M		200 600	
On-State Current RMS (All Conduction Angles; T <sub>C</sub> = 80°C)	I <sub>T(RMS)</sub>	0.8	A
Peak Non-repetitive Surge Current (1/2 Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 25°C)	I <sub>TSM</sub>	8.0	A
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	0.4	A <sup>2</sup> s
Forward Peak Gate Power $(T_C = 80^{\circ}C, t = 1.0 \ \mu s)$	P <sub>GM</sub>	0.1	W
Average Gate Power (T <sub>C</sub> = 80°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.01	W
Operating Junction Temperature Range	TJ	-40 to +110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

#### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient PCB Mounted per Figure 1	$R_{\thetaJA}$	156	°C/W
Thermal Resistance, Junction-to-Tab Measured on Anode Tab Adjacent to Epoxy	$R_{\theta JT}$	25	°C/W
Maximum Device Temperature for Solder- ing Purposes (for 10 Seconds Maximum)	ΤL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

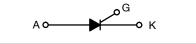
 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant source such that the voltage ratings of the devices are exceeded.



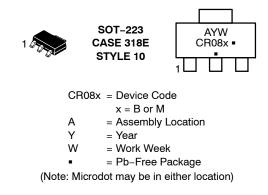
## **ON Semiconductor®**

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SCRs 0.8 AMPERES RMS 200 thru 600 VOLTS







PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MCR08BT1G	SOT-223 (Pb-Free)	1000/Tape &Reel
MCR08MT1G	SOT-223 (Pb-Free)	1000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

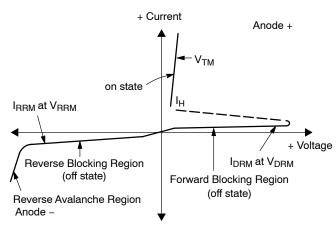
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	-		-		
Peak Repetitive Forward or Reverse Blocking Current (Note 3)	I <sub>DRM</sub> , I <sub>RRM</sub>				
(V <sub>AK</sub> = Rated V <sub>DRM</sub> or V <sub>RRM</sub> , R <sub>GK</sub> = 1 kΩ T <sub>J</sub> = 25°C T <sub>J</sub> = 110°C		-	_	10 200	μΑ μΑ
ON CHARACTERISTICS		_	_	200	μΛ
Peak Forward On-State Voltage (Note 2) (I <sub>T</sub> = 1.0 A Peak)	V <sub>TM</sub>	-	-	1.7	V
Gate Trigger Current (Continuous dc) (Note 4) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 $\Omega$ )	I <sub>GT</sub>	-	-	200	μA
Holding Current (Note 3) (V <sub>AK</sub> = 12 Vdc, Initiating Current = 20 mA)		-	-	5.0	mA
Gate Trigger Voltage (Continuous dc) (Note 4) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 $\Omega$ )		-	-	0.8	V
Turn–On Time ( $V_{AK}$ = 12 Vdc, $I_{TM}$ = 5 Adc, $I_{GT}$ = 5 mA) t		-	1.25	-	μs
DYNAMIC CHARACTERISTICS					
Critical Rate-of-Rise of Off State Voltage ( $V_{pk}$ = Rated V <sub>DRM</sub> , T <sub>C</sub> = 110°C, R <sub>GK</sub> = 1 k $\Omega$ , Exponential Method)	dv/dt	10	_	_	V/μs

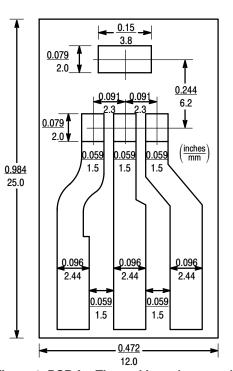
2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

3.  $R_{GK} = 1000 \Omega$  is included in measurement. 4.  $R_{GK}$  is not included in measurement.

Symbol	Parameter	
V <sub>DRM</sub>	Peak Repetitive Off State Forward Voltage	
I <sub>DRM</sub>	Peak Forward Blocking Current	
V <sub>RRM</sub>	Peak Repetitive Off State Reverse Voltage	
I <sub>RRM</sub>	Peak Reverse Blocking Current	
V <sub>TM</sub>	Peak On State Voltage	
Ι <sub>Η</sub>	Holding Current	I <sub>RRM</sub> at V <sub>RRM</sub>

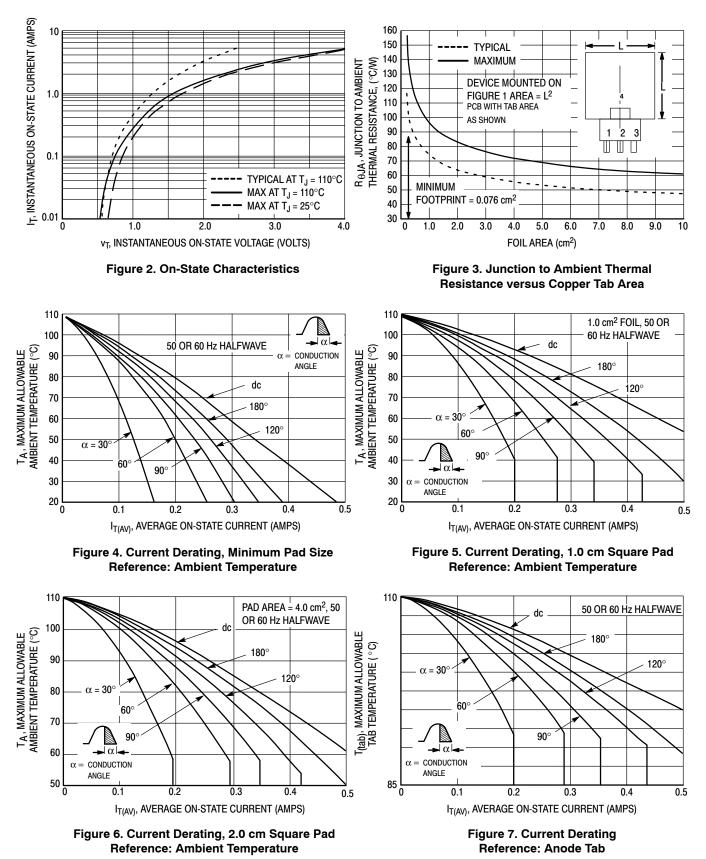
#### **Voltage Current Characteristic of SCR**





BOARD MOUNTED VERTICALLY IN CINCH 8840 EDGE CONNECTOR. BOARD THICKNESS = 65 MIL., FOIL THICKNESS = 2.5 MIL. MATERIAL: G10 FIBERGLASS BASE EPOXY

Figure 1. PCB for Thermal Impedance and Power Testing of SOT-223



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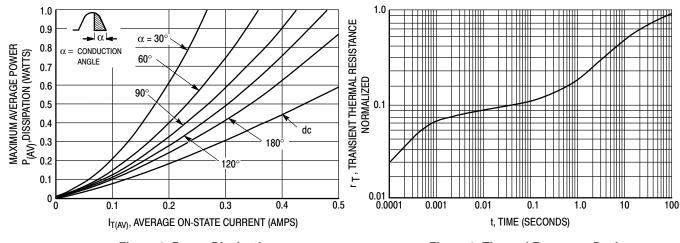


Figure 8. Power Dissipation

Figure 9. Thermal Response Device Mounted on Figure 1 Printed Circuit Board

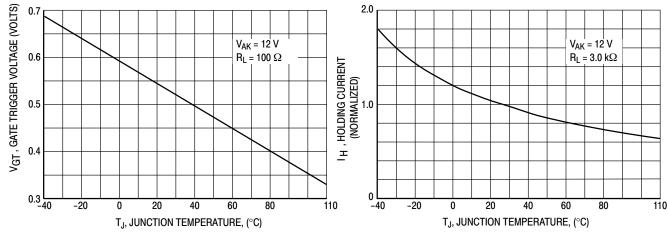
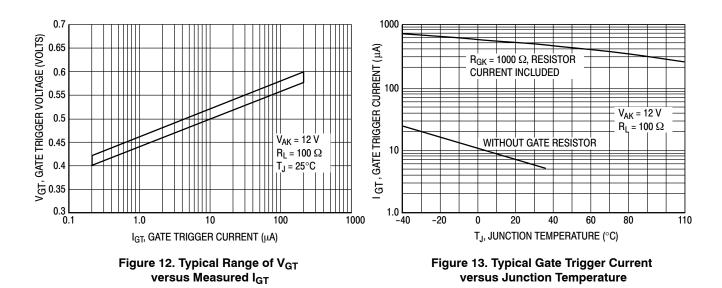
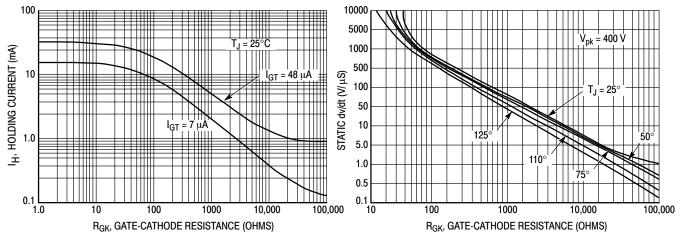


Figure 10. Typical Gate Trigger Voltage versus Junction Temperature

Figure 11. Typical Normalized Holding Current versus Junction Temperature





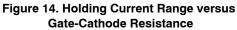
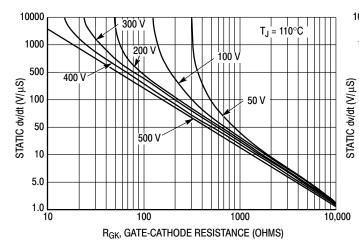
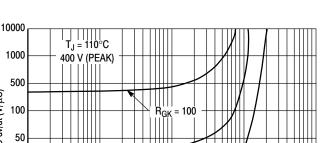


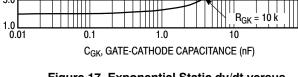
Figure 15. Exponential Static dv/dt versus Junction **Temperature and Gate-Cathode Termination Resistance** 





10

5.0

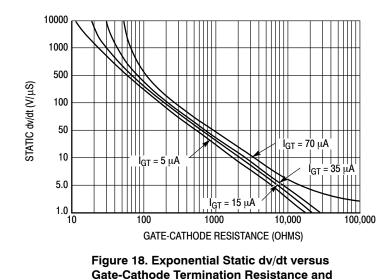


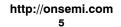
100

R<sub>GK</sub> = 1.0

Figure 16. Exponential Static dv/dt versus Peak Voltage and Gate-Cathode Termination Resistance

Figure 17. Exponential Static dv/dt versus **Gate-Cathode Capacitance and Resistance** 

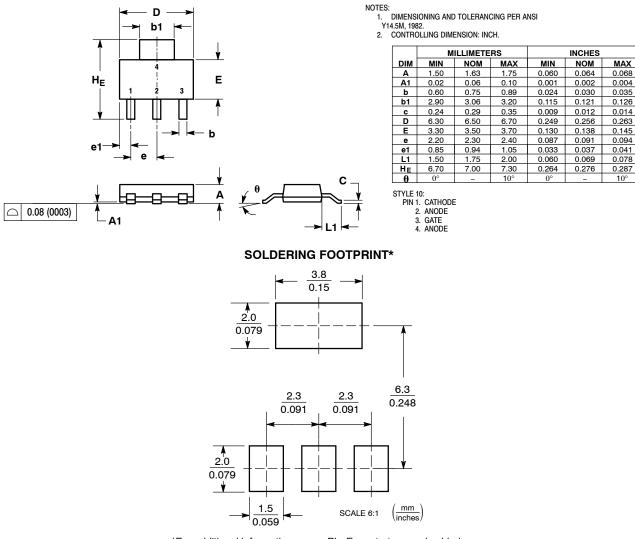




**Product Trigger Current Sensitivity** 

#### PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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